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TOSHIBA Transistor Silicon PNP Epitaxial Type

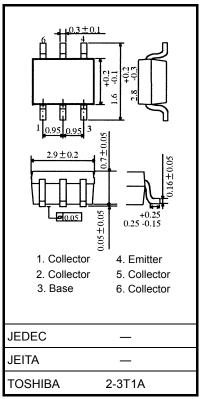
TPC6603

Switching Applications DC/DC Converter Applications Strobe Flash Applications

- High DC current gain: h_{FE} = 200 to 500 (I_C = -0.5 A)
- Low collector-emitter saturation: V_{CE (sat)} = -0.19 V (max)
- High-speed switching: t_f = 40 ns (typ.)

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Characteristic		Symbol	Rating	Unit				
Collector-base voltage		V _{CBO}	-30	V				
Collector-emitter voltage		V _{CEO}	-20	V				
Emitter-base voltage		V _{EBO}	-7	V				
Collector current	DC	Ι _C	-3.0	A				
	Pulse	I _{CP}	-5.0					
Base current		Ι _Β	-0.3	mA				
Collector power dissipation	DC		0.8	W				
	t = 10 s	P _C (Note 1)	1.6					
Junction temperature		Тj	150	°C				
Storage temperature range		T _{stg}	-55 to 150	°C				

Absolute Maximum Ratings (Ta = 25°C)



Weight: 0.01 g (typ.)

Note 1: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm²)

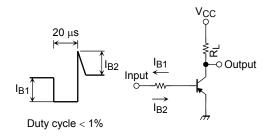
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

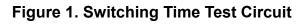
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Мах	Unit
Collector cutoff current		I _{CBO}	$V_{CB} = -30 \text{ V}, \text{ I}_{E} = 0$			-100	nA
Emitter cutoff current		I _{EBO}	$V_{EB} = -7 V, I_C = 0$	_		-100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_{C} = -10 \text{ mA}, I_{B} = 0$	-20	_	_	V
DC current gain		h _{FE} (1)	$V_{CE} = -2 V$, $I_C = -0.5 A$	200	_	500	
		h _{FE} (2)	$V_{CE} = -2 V$, $I_C = -1.6 A$	100	_		
Collector-emitter saturation voltage		V _{CE (sat)}	$I_{C} = -1.6 \text{ A}, I_{B} = -53 \text{ mA}$	_	_	-0.19	V
Base-emitter saturation voltage		V _{BE (sat)}	$I_{C} = -1.6 \text{ A}, I_{B} = -53 \text{ mA}$	_	_	-1.10	V
Collector output capacitance		C _{ob}	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	28		pF
Switching time	Rise time	tr	See Figure 1 circuit diagram $V_{CC} \simeq -12 \text{ V}, \text{ R}_L = 7.5 \Omega$ $I_{B1} = -I_{B2} = -53.3 \text{ mA}$	_	70		
	Storage time	t _{stg}			150		ns
	Fall time	t _f			40		





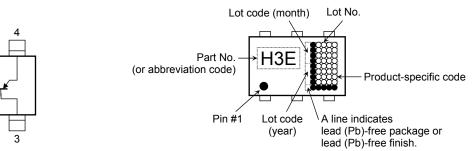
Circuit configuration (Top View)

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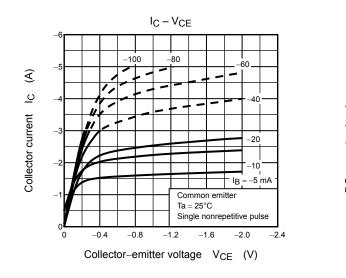
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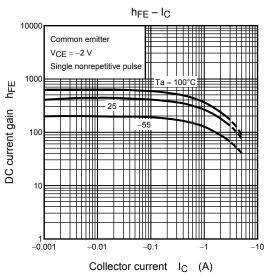
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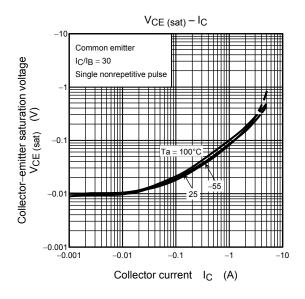


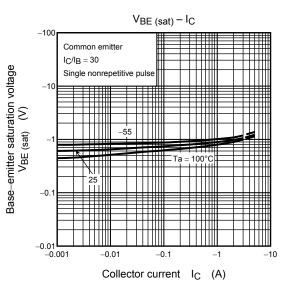


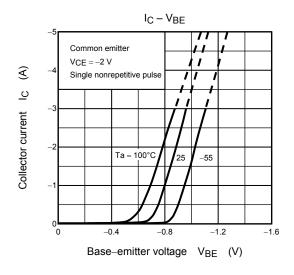
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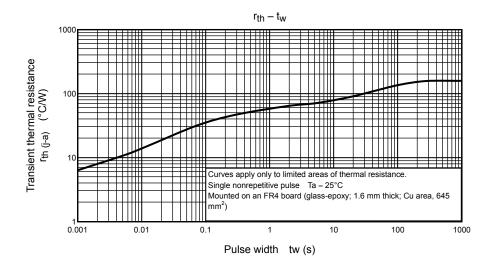












Safe operating area -10 IC max (pulse) * 10 ms* 1 ms* 100 μs* 10 μs* IC max (continuous) 1111 Þ 10 s* <u>ں</u> 100 ms* Collector current (Ta = 25°C) TT (1a = 25°C)
 *: Single nonrepetitive pulse Ta = 25°C
 Note that the curves for 100 ms, 10 s and DC operation will be different when the devices are not mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm²).
 These characteristic curves must be derated linearly with increase in temperature. -0.1 max VCEO --0.01 -0.1 -1 -10 -100 $Collector-emitter \ voltage \quad V_{CE} \quad (V)$

RESTRICTIONS ON PRODUCT USE

20070701-EN

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